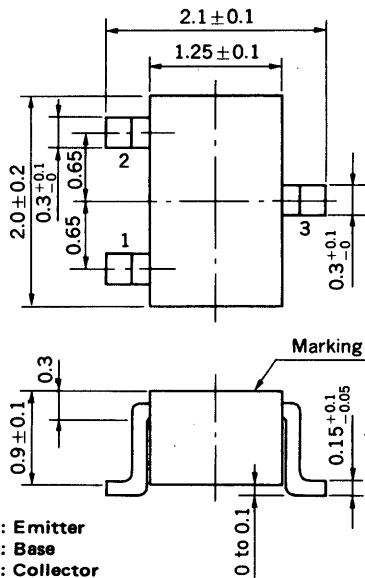
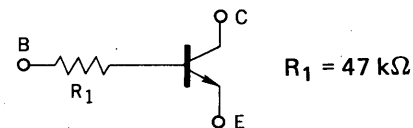


**MEDIUM SPEED SWITCHING**  
**RESISTOR BUILT-IN TYPE NPN TRANSISTOR**
**PACKAGE DIMENSIONS**  
 in millimeters
**FEATURES**

- Resistor Built-in TYPE



- Complementary to GN1L4Z

**ABSOLUTE MAXIMUM RATINGS**Maximum Voltages and Currents ( $T_a = 25^\circ\text{C}$ )

Collector to Base Voltage	$V_{CBO}$	60	V
Collector to Emitter Voltage	$V_{CEO}$	50	V
Emitter to Base Voltage	$V_{EBO}$	5	V
Collector Current (DC)	$I_C$	100	mA
Collector Current (Pulse)	$I_C$	200	mA

Maximum Power Dissipation

Total Power Dissipation at $25^\circ\text{C}$ Ambient Temperature	$P_T$	150	mW
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Maximum Temperatures

Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	$I_{CBO}$			100	nA	$V_{CB} = 50\text{ V}, I_E = 0$
DC Current Gain	$h_{FE1}^*$	135	270	600		$V_{CE} = 5.0\text{ V}, I_C = 5.0\text{ mA}$
DC Current Gain	$h_{FE2}^*$	100	260			$V_{CE} = 5.0\text{ V}, I_C = 50\text{ mA}$
Collector Saturation Voltage	$V_{CE(sat)}^*$		0.05	0.2	V	$I_C = 5.0\text{ mA}, I_B = 0.25\text{ mA}$
Low-Level Input Voltage	$V_{IL}^*$		0.57	0.5	V	$V_{CE} = 5.0\text{ V}, I_C = 100\text{ }\mu\text{A}$
High-Level Input Voltage	$V_{IH}^*$	4.0	1.7		V	$V_{CE} = 0.2\text{ V}, I_C = 5.0\text{ mA}$
Input Resistor	$R_1$	32.9	47.0	61.1	k $\Omega$	
Turn-on Time	$t_{on}$			0.2	$\mu\text{s}$	$V_{CC} = 5\text{ V}, V_{in} = 5\text{ V}$ $R_L = 1\text{ k}\Omega$ $PW = 2\text{ }\mu\text{s}, \text{Duty Cycle} \leq 2\%$
Storage Time	$t_{stg}$			5.0	$\mu\text{s}$	
Turn-off Time	$t_{off}$			6.0	$\mu\text{s}$	

\* Pulsed:  $PW \leq 350\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$  **$h_{FE}$  Classification**

Marking	L61	L62	L63
$h_{FE1}$	135 to 270	200 to 400	300 to 600

TYPICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )